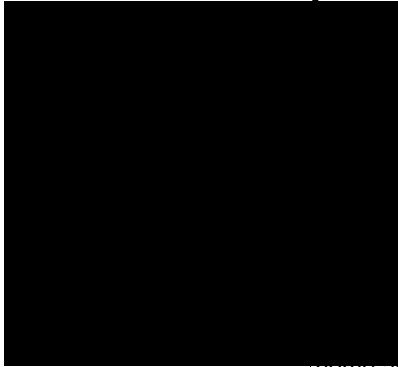


## Super Fast Recovery Bridge Rectifiers



### Features

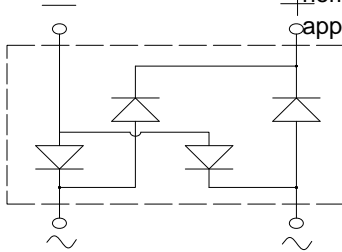
- UL recognition, file #E313149
- Ideal for automated placement
- Glass passivated chip junction
- High surge current capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

### Typical Applications

GeneralV arger,

home appliances, office equipment, and telecommunication

applications.



### Mechanical Data

**Package:** ABS

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, Halogen free

**Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102

**Polarity:** As marked on body

### Maximum Ratings (T<sub>a</sub>=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	EABS6
Device marking code			EABS6
Maximum Repetitive Peak Reverse Voltage	VRRM	V	600
Maximum RMS Voltage	VRMS	V	420
Maximum DC blocking Voltage	VDC	V	600
Average rectified output current @60Hz sine wave, R-load, T <sub>c</sub> =130	I <sub>O</sub>	A	1.0
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, T <sub>j</sub> =25	I <sub>FSM</sub>	A	30
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, T <sub>j</sub> =25			60
Current squared time @1ms t<8.3ms T <sub>j</sub> =25 Rating of per diode	I <sup>2</sup> t	A <sup>2</sup> s	3.74
Storage temperature	T <sub>stg</sub>		-55 ~ +150
Junction temperature	T <sub>j</sub>		-55 ~ +150

### Electrical Characteristics T<sub>a</sub>=25 Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	EABS6
Maximum reverse recovery time	t <sub>r</sub>	ns	I <sub>f</sub> =0.5A, I <sub>r</sub> =1.0A, I <sub>r</sub> =0.25A	35
Maximum instantaneous forward voltage drop per diode	V <sub>F</sub>	V	IFM=0.5A	1.7
Maximum DC reverse current at rated DC blocking voltage per diode	I <sub>R</sub>	μA	T <sub>j</sub> =25	5
			T <sub>j</sub> =125	100
Typical junction capacitance	C <sub>j</sub>	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	13



# EABS6

## Thermal Characteristics $T_a=25$ Unless otherwise specified

PARAMETER		SYMBOL	UNIT	EABS6
Thermal Resistance	Between junction and ambient	R J-A	/W	62.5
	Between junction and lead	R J-L		25.0
	Between junction and case	R J-C		8.0

Note: Device mounted on P.C.B with  $T_a=25$  ER





# EABS6

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## Disclaimer

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